Methods for Forming a Structured Metallization on a Semiconductor Wafer

Abstract

The present invention relates to a method of forming a structured metallization (30) on a semiconductor wafer (20), wherein a main surface of the wafer (20) has a passivation layer (22) applied thereto, which is structured so as to determine at least one bond pad (24). Initially, a metal bump (26) is produced on the at least one bond pad (24). An activated dielectric (28) is then produced on the areas of the passivation layer (22) on which the structured metallization (30) is to be formed. Finally, metal is chemically deposited directly on the activated dielectric (28) and on the metal bump (26) in such a way that the structured metallization formed on the activated dielectric and the metal chemically deposited on the metal bump are electroconductively joined.

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